

**AMENDMENTS TO THE CLAIMS:**

The following listing of claims replaces all prior listings, and all prior versions, of claims in the above-identified application.

**LISTING OF CLAIMS:**

1.-17. (Cancelled).

18. (Currently amended) A manufacturing method for an electronic device that has IC elements, each IC element having electrodes formed respectively on the respective surfaces of a pair of opposed sides thereof, and a first circuit layer and a second circuit layer, comprising:

a step of forming a slit in the first circuit layer or the second circuit layer;

a step of forming (a) a first connecting part for electrically connecting the electrode of one side of the IC elements and the first circuit layer, on the one side, (b) a second connecting part for electrically connecting the electrode of the other side of the IC elements and the second circuit layer, and (c) a third connecting part for electrically connecting the first and second circuit layers so that the second connecting part and the third connecting part are connected spanning the slit; and

a step of positionally aligning the connection surfaces of the IC elements and either one of the circuit layers while continuously supplying the IC elements individually into an IC elements transport mechanism,

wherein the step of continuously supplying the IC elements comprises:

a step of individually holding an IC element in an IC element holding part of an IC elements transport mechanism having not less than one IC element holding part which is formed as a notch shape;

a step of delivering the IC element thus held by running the IC element holding part of the transport mechanism; and

a step of securing the IC element held by the IC element holding part at any of the circuit layers with a temporary securing pin.

19. (Cancelled).

20. (Currently amended) The manufacturing method for an electronic device according to claim 18, wherein the IC elements transport mechanism ~~is step of continuously supplying the IC elements comprises:~~

~~—— a step of individually holding an IC element in an IC element holding part of a disc shaped IC elements transport mechanism having not less than one IC element holding part; and~~

~~—— a step of delivering the IC element thus held by running the IC element holding part of the transport mechanism.~~

21. (Cancelled).

22. (Currently amended) The manufacturing method for an electronic device according to claim 18, wherein the step of continuously supplying the IC elements further comprises:

a step of aligning the IC elements by action of an IC elements alignment/supply mechanism to facilitate individually holding ~~the an~~ IC element in ~~the an~~ IC element holding part of ~~the an~~ IC elements transport mechanism having not less than one IC element holding part; ~~and~~

~~—— a step of delivering the IC element thus held by running the IC element holding part of the transport mechanism.~~

23. (Currently amended) The manufacturing method for an electronic device according to claim 18, wherein the step of continuously supplying the IC elements comprises:

a step of aligning the IC elements by action of an IC elements alignment/supply mechanism which is a line feeder to facilitate individually holding ~~thean~~ IC element in ~~thean~~ IC element holding part of ~~thean~~ IC elements transport mechanism having not less than one IC element holding part; ~~and~~  
~~—— a step of delivering the IC element thus held by running the IC element holding part of the transport mechanism.~~

24. (Currently amended) The manufacturing method for an electronic device according to claim 18, wherein the step of continuously supplying the IC elements comprises:

a step of aligning the IC elements by action of an IC elements alignment/supply mechanism which is a high frequency alignment feeder to facilitate individually holding ~~thean~~ IC element in ~~thean~~ IC element holding part of ~~thean~~ IC elements transport mechanism having not less than one IC element holding part; ~~and~~  
~~—— a step of delivering the IC element thus held by running the IC element holding part of the transport mechanism.~~

25. (Previously presented) The manufacturing method for an electronic device according to claim 18, wherein the electrical connection of an electrode of the IC elements and at least one of the first and the second circuit layers is made via an anisotropic conductive adhesive layer.

26. (Previously presented) The manufacturing method for an electronic device according to claim 18, further comprising:

a step of connecting at once, the electrodes of the IC elements and at least one layer from among the first or the second circuit layers, wherein the step of connecting is after the step of positionally aligning the connection surfaces.

27. (Previously presented) The manufacturing method for an electronic device according to claim 26, wherein the method in that the electrodes of the IC elements and at least one layer from among the first and the second circuit layers are connected at once is realized by thermal compression.

28. (Previously presented) The manufacturing method for an electronic device according to claim 27, wherein the gaps between the first and second circuit layers are sealed by the thermal compression.

29. (Previously presented) The manufacturing method for an electronic device according to claim 26, further comprising:

a step of cutting a continuum of a plurality of the IC elements into individual pieces, wherein the step of cutting is after the step of connecting, at once, a plurality of the IC elements with at least one from among the first and the second circuit layers.

30. (Previously presented) The manufacturing method for an electronic device according to claim 18, wherein a conductive layer is formed on the surface of at least one from among the first and the second circuit layers.

31. (Previously presented) The manufacturing method for an electronic device according to claim 28, wherein the first and second circuit layers include aluminum.

32. (Previously presented) The manufacturing method for an electronic device according to claim 28, wherein at least one from among the first and second circuit layers is supported on a base substrate comprised of an organic resin, and that this organic resin be selected from the group consisting of polyvinyl chloride (PVC), acrylonitrile butadiene styrene (ABS), polyethylene terephthalate (PET), polyethylene terephthalate glycol (PETG), polyethylene naphthalate (PEN), polycarbonate resin (PC), biaxial polyester (O-PET), and polyimide resin.

33. (Previously presented) The manufacturing method for an electronic device according to claim 28, wherein either one of the first or the second circuit layer is supported on a base substrate comprised of paper.

34. (Previously presented) The manufacturing method for an electronic device according to claim 18, wherein electrical connections of electrodes of the IC elements and the first and second circuit layers are made via first and second anisotropic conductive adhesive layers, respectively, and a total thickness of the first and second anisotropic conductive adhesive layers is not less than half the thickness of the IC elements.